

December 2014

H11G1M, H11G2M 6-Pin DIP High Voltage Photodarlington Optocouplers

Features

- High BV_{CEO}:
 - 100 V Minimum for H11G1M
 - 80 V Minimum for H11G2M
- High Sensitivity to Low Input Current (Minimum 500% CTR at I_F = 1 mA)
- Low Leakage Current at Elevated Temperature (Maximum 100 μA at 80°C)
- Safety and Regulatory Approvals:
 - UL1577, 4,170 VAC_{RMS} for 1 Minute
 - DIN-EN/IEC60747-5-5, 850 V Peak Working Insulation Voltage

Applications

- CMOS Logic Interface
- Telephone Ring Detector
- Low Input TTL Interface
- Power Supply Isolation
- Replace Pulse Transformer

General Description

The H11G1M and H11G2M are photodarlington-type optically coupled optocouplers. These devices have a gallium arsenide infrared emitting diode coupled with a silicon darlington connected phototransistor which has an integral base-emitter resistor to optimize elevated temperature characteristics.

Schematic

ANODE 1 6 BASE CATHODE 2 5 COLLECTOR 4 EMITTER

Figure 1. Schematic

Package Outlines

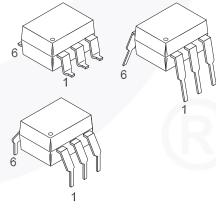


Figure 2. Package Outlines

Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
Installation Classifications per DIN VDE	< 150 V _{RMS}	I–IV
0110/1.89 Table 1, For Rated Mains Voltage	< 300 V _{RMS}	I–IV
Climatic Classification		55/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
\/	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$, Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	1360	V _{peak}
V _{PR}	Input-to-Output Test Voltage, Method B, V _{IORM} x 1.875 = V _{PR} , 100% Production Test with t _m = 1 s, Partial Discharge < 5 pC	1594	V _{peak}
V _{IORM}	Maximum Working Insulation Voltage	850	V _{peak}
V _{IOTM}	Highest Allowable Over-Voltage	6000	V _{peak}
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
T _S	Case Temperature ⁽¹⁾	175	°C
I _{S,INPUT}	Input Current ⁽¹⁾	350	mA
P _{S,OUTPUT}	Output Power ⁽¹⁾	800	mW
R _{IO}	Insulation Resistance at T _S , V _{IO} = 500 V ⁽¹⁾	> 10 ⁹	Ω

Note:

1. Safety limit values – maximum values allowed in the event of a failure.

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Value	Unit	
TOTAL DEVIC	E			
T _{STG}	Storage Temperature	-40 to +125	°C	
T _{OPR}	Operating Temperature	-40 to +100	°C	
T _J	Junction Temperature	-40 to +125	°C	
T _{SOL}	Lead Solder Temperature	260 for 10 seconds	°C	
В	Total Device Power Dissipation @ T _A = 25°C	290	mW	
P_{D}	Derate Above 25°C	3.5	mW/°C	
EMITTER				
I _F	Forward Input Current	60	mA	
V_{R}	Reverse Input Voltage	6.0	V	
I _F (pk)	Forward Current – Peak (1 µs pulse, 300 pps)	3.0	Α	
	LED Power Dissipation @ T _A = 25°C	90	mW	
P_{D}	Derate Above 25°C	1.8	mW/°C	
DETECTOR				
	Collector-Emitter Voltage			
V_{CEO}	H11G1M	100	V	
	H11G2M	80	V	
В	Photodetector Power Dissipation @ T _A = 25°C	200	mW	
P_{D}	Derate Above 25°C	2.67	mW/°C	

Electrical Characteristics

 $T_A = 25$ °C unless otherwise specified.

Individual Component Characteristics

Symbol	Characteristic	Test Conditions	Device	Min.	Тур.	Max.	Unit	
EMITTER	EMITTER							
V _F	Forward Voltage	I _F = 10 mA	All		1.3	1.5	V	
$\frac{\Delta V_F}{\Delta T_A}$	Forward Voltage Temperature Coefficient		All		-1.8		mV/°C	
BV_R	Reverse Breakdown Voltage	I _R = 10 μA	All	3.0	25		V	
C	Junction Consoitance	V _F = 0 V, f = 1 MHz	All		50		pF	
C_{J}	Junction Capacitance	V _F = 1 V, f = 1 MHz	All		65		pF	
I _R	Reverse Leakage Current	V _R = 3.0V	All		0.001	10	μΑ	
DETECTO	DR						•	
D\/	Breakdown Voltage	I _C = 1.0 mA, I _F = 0	H11G1M	100			V	
BV _{CEO}	Collector to Emitter		H11G2M	80			V	
D\/	Collector to Base Ic = 100 µA	H11G1M	100			V		
BV _{CBO}	Collector to base	I _C = 100 μA	H11G2M	80			V	
BV _{EBO}	Emitter to Base		All	7	10		V	
	Leakage Current Collector to Emitter	V _{CE} = 80 V, I _F = 0	H11G1M			100	nA	
		V _{CE} = 60 V, I _F = 0	H11G2M			100	nA	
		V _{CE} = 80 V, I _F = 0, T _A = 80°C	H11G1M			100	μA	
		V _{CE} = 60 V, I _F = 0, T _A = 80°C	H11G2M			100	μA	

Transfer Characteristics

Symbol	Characteristics	Test Conditions	Device	Min.	Тур.	Max.	Unit
EMITTER					<u></u>		
CTR Current Transfer Ratio,	I _F = 10 mA, V _{CE} = 1 V	All	100 (1000)			mA (%)	
Collector to Emitter		I _F = 1 mA, V _{CE} = 5 V	All	5 (500)			mA (%)
\/	Cotumetics Voltage	I _F = 16 mA, I _C = 50 mA	All		0.85	1.0	V
V _{CE(SAT)}	Saturation Voltage	I _F = 1 mA, I _C = 1 mA	All		0.75	1.0	V
SWITCHING	TIMES						
t _{ON}	Turn-on Time	$R_L = 100 \Omega, I_F = 10 \text{ mA},$	All		5		μs
t _{OFF}	Turn-off Time	V_{CE} = 5 V, f \leq 30 Hz, Pulse Width \leq 300 µs	All		100		μs

Isolation Characteristics

Symbol	Characteristic	Test Conditions	Min.	Тур.	Max.	Unit
V _{ISO}	Input-Output Isolation Voltage	t = 1 Minute	4170			VAC _{RMS}
C _{ISO}	Isolation Capacitance	V _{I-O} = 0 V, f = 1 MHz		0.2		pF
R _{ISO}	Isolation Resistance	V _{I-O} = ±500 VDC, T _A = 25°C	10 ¹¹			Ω

Typical Performance Curves

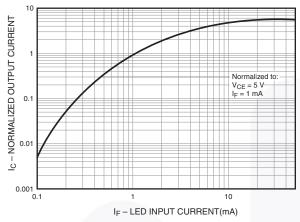


Figure 3. Output Current vs. Input Current

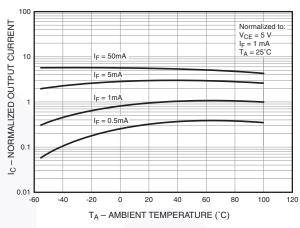


Figure 4. Normalized Output Current vs. Temperature

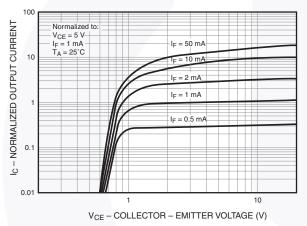


Figure 5. Output Current vs. Collector-Emitter Voltage

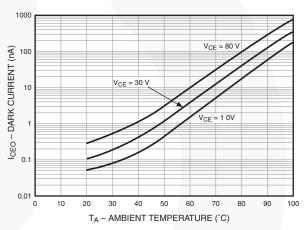


Figure 6. Collector-Emitter Dark Current vs. Ambient Temperature

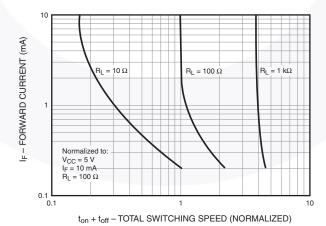


Figure 7. Input Current vs. Total Switching Speed (Typical Values)

Reflow Profile

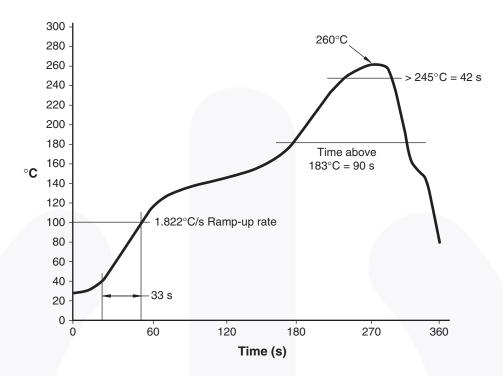


Figure 8. Reflow Profile

Ordering Information

Part Number	Package	Packing Method
H11G1M	DIP 6-Pin	Tube (50 Units)
H11G1SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
H11G1SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
H11G1VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11G1SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
H11G1SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
H11G1TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

Note:

2. The product orderable part number system listed in this table also applies to the H11G2M device.

Marking Information

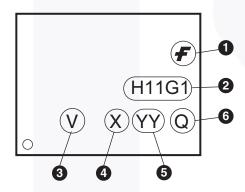


Figure 9. Top Mark

Table 1. Top Mark Definitions

1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., "4"
5	Digit Work Week, Ranging from "01" to "53"
6	Assembly Package Code







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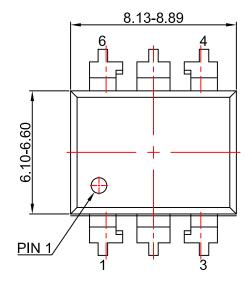
LAND PATTERN RECOMMENDATION

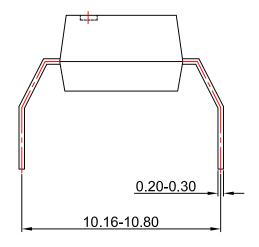


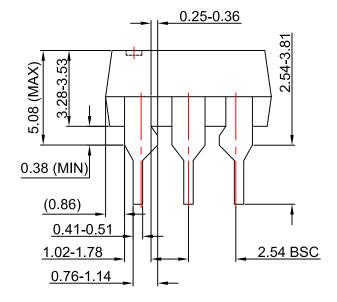


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